

Si APD

S15414 series

High-speed, compact Si APD that does not require temperature adjustment

The S15414 series is a gain-stabilized APD (GS APD) with a built-in temperature compensation function inside the sensor. This realizes constant gain without the need for temperature adjustment. It is suitable for laser monitors of optical rangefinders used in a wide range of applications, from consumer to industrial.

Features

- **■** Built-in temperature compensation function
- Compact package: 2.0 × 1.8 × 0.85^t mm
- Peak sensitivity wavelength: 800 nm (M=50)
- → High-speed response: Cutoff frequency=1.2 GHz typ. (S15414-02, λ=800 nm, M=50)

Applications

Optical rangefinders

Structure

Parameter	S15414-02	S15414-05	Unit	
Photosensitive area*1	ф0.2	ф0.5	mm	
Package	Glass epoxy			
Seal material	Silicone resin			

^{*1:} Area in which a typical gain can be obtained

■ Absolute maximum ratings

Parameter	Symbol	Specification	
Anode reverse current (DC)	IR anode max	0.1	mA
Forward current	IF max	10	mA
Operating temperature*2	Topr	-30 to +105	°C
Storage temperature*2	Tstg	-40 to +105	°C
Soldering temperature	Tsol	260 (3 times)*3	°C

^{*2:} No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environments, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

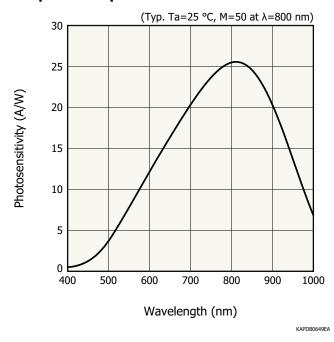
^{*3:} Reflow soldering, JEDEC J-STD-020 MSL 2a, see P.5

■ Electrical and optical characteristics (Ta=25 °C, unless otherwise noted)

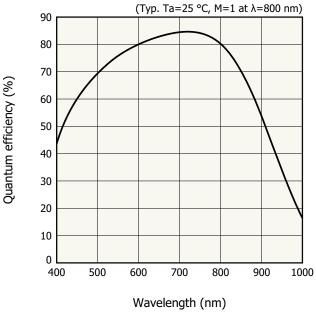
Dayamatar	Symbol Condition		S15414-02		S15414-05		l lmit		
Parameter	Symbol	Condition	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Spectral response range	Spectral response range λ		400 to 1000					nm	
Peak sensitivity wavelength	λр		-	800	-	-	800	-	nm
Photosensitivity	S	λ=800 nm, M=1	-	0.52	-	-	0.52	-	A/W
Quantum efficiency	QE	λ=800 nm, M=1	-	80	-	-	80	-	%
Operating reverse voltage	Vop	Gain-stabilized mode operation*4	140 + 0.63 × (Ta opr -25)*5	-	-	140 + 0.63 × (Ta opr -25)*5	-	-	V
Temperature coefficient of operating reverse voltage	ΔTVop		-	0.63	-	-	0.63	-	V/°C
Dark current	current ID Gain-stabilized mode operation		-	15	150	-	30	300	pА
Dark current temperature coefficient	mperature ΔTID M=50		-	1.1	-	-	1.1	-	times/°C
Cutoff frequency fc $M=50$, RL= 50Ω $\lambda=800$ nm, -3 dE		M=50, RL=50 Ω λ=800 nm, -3 dB	-	1.2	-	-	1.0	-	GHz
Terminal capacitance	Ct	M=50, f=1 MHz	-	0.6	-	-	1.4	-	pF
Excess noise figure	Х	M=50, λ=800 nm	-	0.3	-	-	0.3	-	-
Gain	М	Gain-stabilized mode operation*4, λ =800 nm		50	60	40	50	60	-
Gain control range	-	λ=800 nm	-	30 to 100	-	-	30 to 100	-	-

^{*4:} Apply bias voltage to anode. IR anode limit=10 μA , guard pin=GND

- Spectral response



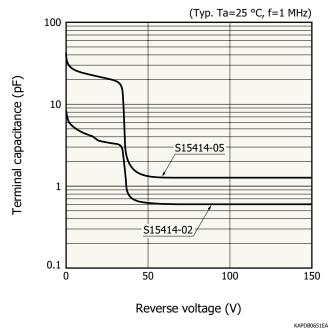
- Quantum efficiency vs. wavelength



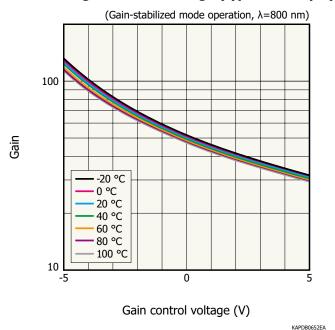
KAPDB0650EA

^{*5:} Ta opr=assumed maximum operating temperature

Terminal capacitance vs. reverse voltage

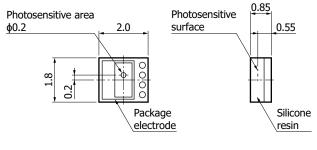


Gain vs. gain control voltage (typical example)

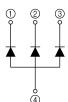


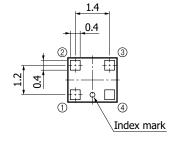
Dimensional outlines (unit: mm)

S15414-02



Tolerance unless otherwise noted: ± 0.2 Chip position accuracy with respect to package electrode pattern center: X, Y $\leq \pm 0.2$

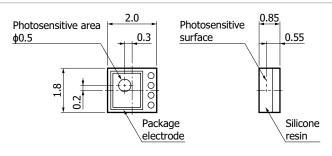


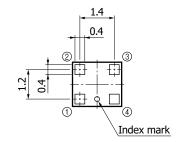


1	Gain control	Gain control voltage input (connect to GND)
2	Output	APD output
3	Guard	Leakage current output (connect to GND)
4	Anode	Bias voltage input

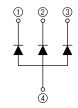
KAPDA0229EA

S15414-05





Tolerance unless otherwise noted: ± 0.2 Chip position accuracy with respect to package electrode pattern center: X, Y $\leq \pm 0.2$



1	Gain control	Gain control voltage input (connect to GND)
2	Output	APD output
3	Guard	Leakage current output (connect to GND)
4	Anode	Bias voltage input

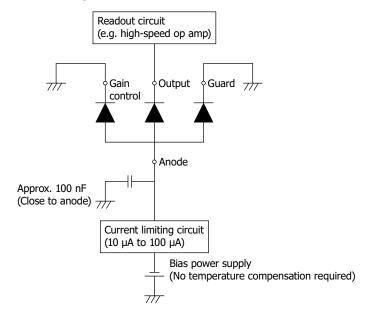
KAPDA0230EA

Recommended land pattern

0.4

KAPDC0138EA

- Connection example



- \cdot Connection to a bias power supply and a current limiting circuit are essential.
- The gain can be controlled by applying a voltage to the gain pin.
- · We recommend connecting a capacitor near the anode pin to stabilize the bias voltage.

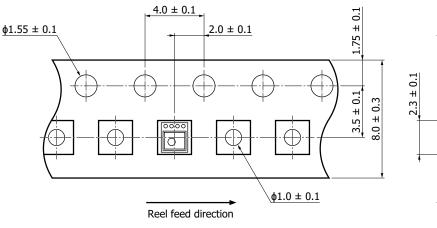
KAPDC0137EB

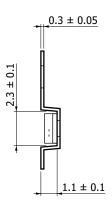
Standard packing specifications

■ Reel (conforms to JEITA ET-7200)

Appearance	Hub diameter	Tape width	Material	Electrostatic characteristics
ф180 mm	ф60 mm	8 mm	PS	Conductive

■ Embossed tape (unit: mm, material: PS, conductive)



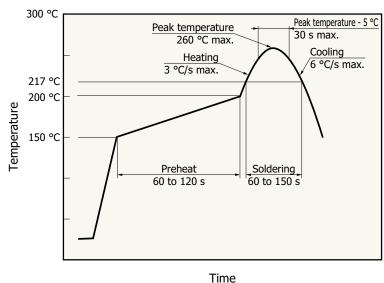


KAPDC0139EA

- Packing quantity 1000 pcs/reel
- Packing state

 Reel and desiccant in moisture-proof packaging (vacuum-sealed)

Recommended reflow soldering conditions



- · After unpacking, store in an environment at a temperature of 30 °C or less and a humidity of 60% or less, and perform reflow soldering within 4 weeks.
- The effect that the product receives during reflow soldering varies depending on the circuit board and reflow oven that are used. When you set reflow soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

KMPDB0405EC

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Baking

If 12 months have passed without unpacking or the above storage period has passed after unpacking, perform baking before reflow soldering to dehumidify. For the baking, refer to "Precautions / Surface mount type products" in the related information.

- Recommended baking conditions
- · Temperature: 150 °C, 3 hours, up to twice

Note: When you set baking conditions, check that problems do not occur in the product by testing out the conditions in advance.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
- Disclaimer
- Precautions / Surface mount type products
- Catalogs
- · Technical note / Si APD

The content of this document is current as of February 2025.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

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